

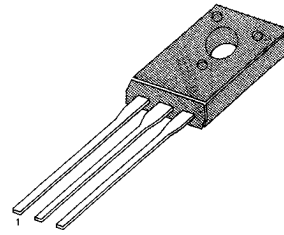
BD234/236/238**PNP EPITAXIAL SILICON TRANSISTOR****MEDIUM POWER LINEAR AND SWITCHING APPLICATIONS**

- Complement to BD 233/235/237 respectively

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector Base Voltage : BD234	V_{CBO}	- 45	V
: BD236		- 60	V
: BD238		- 100	V
Collector Emitter Voltage : BD234	V_{CEO}	- 45	V
: BD236		- 60	V
: BD238		- 80	V
Collector Emitter Voltage : BD234	V_{CER}	- 45	V
: BD236		- 60	V
: BD238		- 100	V
Emitter Base Voltage	V_{EBO}	- 5	V
Collector Current (DC)	I_C	- 2	A
Collector Current (Pulse)	I_C	- 6	A
Collector Dissipation ($T_C=25^\circ\text{C}$)	P_C	25	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-65 ~ 150	$^\circ\text{C}$

TO-126



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
* Collector Emitter Sustaining Voltage : BD234	$V_{CEO(SUS)}$	$I_C = - 100\text{mA}, I_B = 0$	- 45			V
: BD236			- 60			V
: BD238			- 80			V
Collector Cutoff Current : BD234	I_{CBO}	$V_{CB} = - 45\text{V}, I_E = 0$			- 100	μA
: BD236		$V_{CB} = - 60\text{V}, I_E = 0$			- 100	μA
: BD238		$V_{CB} = - 100\text{V}, I_E = 0$			- 100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = - 5\text{V}, I_C = 0$			- 1	mA
* DC Current Gain	h_{FE}	$V_{CE} = - 2\text{V}, I_C = - 150\text{mA}$	40			
		$V_{CE} = - 2\text{V}, I_C = - 1\text{A}$	25			
* Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = - 1\text{A}, I_B = - 0.1\text{A}$			- 0.6	V
* Base Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = - 2\text{V}, I_C = - 1\text{A}$			- 1.3	V
Current Gain Bandwidth Product	f_T	$V_{CE} = - 10\text{V}, I_C = - 250\text{mA}$	3			MHz

* Pulse Test : $PW=300\mu\text{s}$, duty Cycle $\leq 1.5\%$ Pulsed

